

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0066] with the following amended paragraph:

[0066] In the first embodiment of the present invention, the blocking layer 144 corresponding to the channel of the thin film transistor is formed, and the data line 132 has a wider width than the related art. Thus, the data line 132 and the pixel electrode 142 have a wider overlap than that of ~~are wider overlapped than~~ the related art. That is, over about 50% of the width of the data line 132 overlaps the pixel electrodes 142. For example, if the data line has a width of over 8 μm , the data line 132 overlaps each of the adjacent pixel electrodes 142 by over 2 μm , respectively, because the formable minimum width of a fine pattern, presently, is about 4 μm and the distance between the adjacent pixel electrodes 142 is about 4 μm . Therefore, since the data line 132 functions as a black matrix and light leakage is blocked around the data line 132, the black matrix can be omitted. Additionally, leakage current in the thin film transistor may be prevented due to the blocking layer 144.